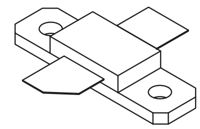
The RF Sub–Micron MOSFET Line
RF Power Field Effect Transistors
N–Channel Enhancement–Mode Lateral MOSFETs

MRF9045R1
MRF9045LSR1

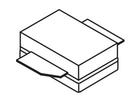
945 MHz, 45 W, 28 V
LATERAL N–CHANNEL
BROADBAND
RF POWER MOSFETs

Designed for broadband commercial and industrial applications with frequencies up to 1.0 GHz. The high gain and broadband performance of these devices make them ideal for large–signal, common–source amplifier applications in 28 volt base station equipment.

- Typical Two–Tone Performance at 945 MHz, 28 Volts
  Output Power — 45 Watts PEP
  Power Gain — 18.8 dB
  Efficiency — 42%
  IMD — –32 dBc
- Integrated ESD Protection
- Designed for Maximum Gain and Insertion Phase Flatness
- Capable of Handling 10:1 VSWR, @ 28 Vdc, 945 MHz, 45 Watts CW Output Power
- Excellent Thermal Stability
- Characterized with Series Equivalent Large–Signal Impedance Parameters
- In Tape and Reel. R1 Suffix = 500 Units per 32 mm, 13 inch Reel.
- Available with Low Gold Plating Thickness on Leads. L Suffix Indicates 40µ″ Nominal.



CASE 360B–05, STYLE 1
NI–360
MRF9045R1



CASE 360C–05, STYLE 1
NI–360S
MRF9045LSR1

MAXIMUM RATINGS

Rating		Symbol	Value	Unit
Drain–Source Voltage		V_{DSS}	65	Vdc
Gate–Source Voltage		V_{GS}	–0.5, +15	Vdc
Total Device Dissipation @ T_C = 25°C Derate above 25°C	MRF9045R1 MRF9045LSR1	P_D	125 0.71 175 1	Watts W/°C
Storage Temperature Range		T_{stg}	–65 to +150	°C
Operating Junction Temperature		T_J	200	°C

THERMAL CHARACTERISTICS

Characteristic		Symbol	Max	Unit
Thermal Resistance, Junction to Case	MRF9045R1 MRF9045LSR1	$R_{\theta JC}$	1.4 1.0	°C/W

ESD PROTECTION CHARACTERISTICS

Test Conditions	Class
Human Body Model	1 (Minimum)
Machine Model	M1 (Minimum)

NOTE – **CAUTION** – MOS devices are susceptible to damage from electrostatic charge. Reasonable precautions in handling and packaging MOS devices should be observed.

REV 7

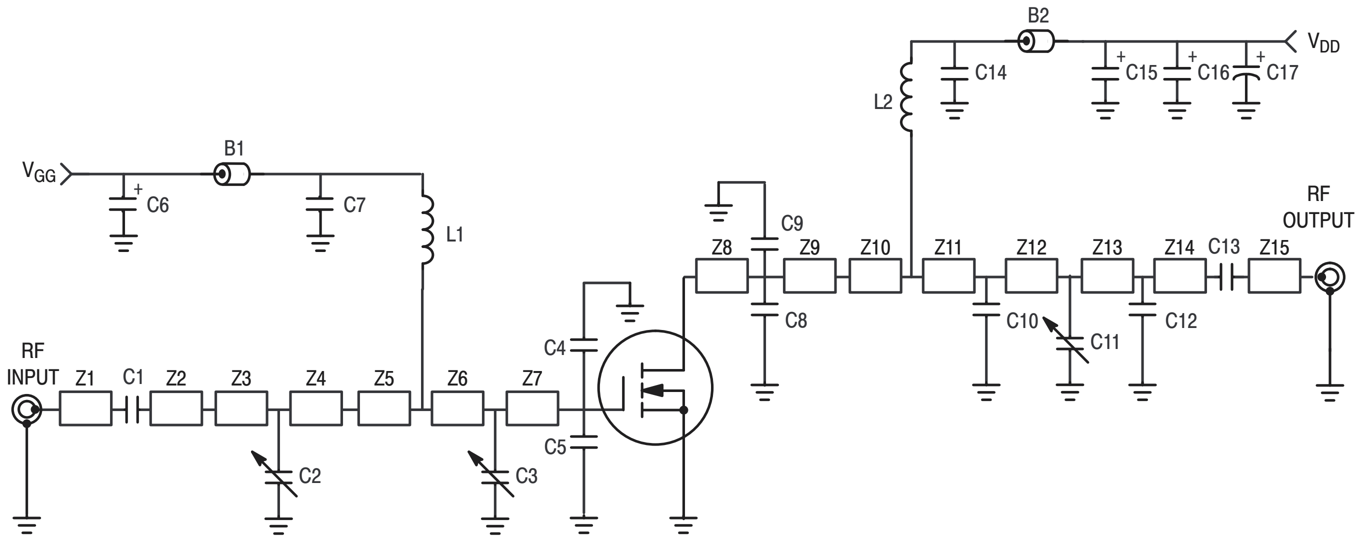
ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Zero Gate Voltage Drain Leakage Current (V_{DS} = 65 Vdc, V_{GS} = 0 Vdc)	I_{DSS}	—	—	10	µAdc
Zero Gate Voltage Drain Leakage Current (V_{DS} = 28 Vdc, V_{GS} = 0 Vdc)	I_{DSS}	—	—	1	µAdc
Gate–Source Leakage Current (V_{GS} = 5 Vdc, V_{DS} = 0 Vdc)	I_{GSS}	—	—	1	µAdc
ON CHARACTERISTICS					
Gate Threshold Voltage (V_{DS} = 10 Vdc, I_D = 150 µAdc)	$V_{GS(th)}$	2	3	4	Vdc
Gate Quiescent Voltage (V_{DS} = 28 Vdc, I_D = 350 mAdc)	$V_{GS(Q)}$	—	3.7	—	Vdc
Drain–Source On–Voltage (V_{GS} = 10 Vdc, I_D = 1 Adc)	$V_{DS(on)}$	—	0.19	0.4	Vdc
Forward Transconductance (V_{DS} = 10 Vdc, I_D = 3 Adc)	g_{fs}	—	4	—	S
DYNAMIC CHARACTERISTICS					
Input Capacitance (V_{DS} = 28 Vdc ± 30 mV(rms)ac @ 1 MHz, V_{GS} = 0 Vdc)	C_{iss}	—	69	—	pF
Output Capacitance (V_{DS} = 28 Vdc ± 30 mV(rms)ac @ 1 MHz, V_{GS} = 0 Vdc)	C_{oss}	—	37	—	pF
Reverse Transfer Capacitance (V_{DS} = 28 Vdc ± 30 mV(rms)ac @ 1 MHz, V_{GS} = 0 Vdc)	C_{rss}	—	1.5	—	pF

(continued)

ELECTRICAL CHARACTERISTICS — continued (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
FUNCTIONAL TESTS (In Motorola Test Fixture, 50 ohm system)					
Two–Tone Common–Source Amplifier Power Gain (V_{DD} = 28 Vdc, P_{out} = 45 W PEP, I_{DQ} = 350 mA, f1 = 945.0 MHz, f2 = 945.1 MHz)	G_{ps}	17	18.8	—	dB
Two–Tone Drain Efficiency (V_{DD} = 28 Vdc, P_{out} = 45 W PEP, I_{DQ} = 350 mA, f1 = 945.0 MHz, f2 = 945.1 MHz)	η	38	42	—	%
3rd Order Intermodulation Distortion (V_{DD} = 28 Vdc, P_{out} = 45 W PEP, I_{DQ} = 350 mA, f1 = 945.0 MHz, f2 = 945.1 MHz)	IMD	—	–32	–28	dBc
Input Return Loss (V_{DD} = 28 Vdc, P_{out} = 45 W PEP, I_{DQ} = 350 mA, f1 = 945.0 MHz, f2 = 945.1 MHz)	IRL	—	–14	–9	dB
Two–Tone Common–Source Amplifier Power Gain (V_{DD} = 28 Vdc, P_{out} = 45 W PEP, I_{DQ} = 350 mA, f1 = 930.0 MHz, f2 = 930.1 MHz and f1 = 960.0 MHz, f2 = 960.1 MHz)	G_{ps}	—	18.5	—	dB
Two–Tone Drain Efficiency (V_{DD} = 28 Vdc, P_{out} = 45 W PEP, I_{DQ} = 350 mA, f1 = 930.0 MHz, f2 = 930.1 MHz and f1 = 960.0 MHz, f2 = 960.1 MHz)	η	—	41	—	%
3rd Order Intermodulation Distortion (V_{DD} = 28 Vdc, P_{out} = 45 W PEP, I_{DQ} = 350 mA, f1 = 930.0 MHz, f2 = 930.1 MHz and f1 = 960.0 MHz, f2 = 960.1 MHz)	IMD	—	–33	—	dBc
Input Return Loss (V_{DD} = 28 Vdc, P_{out} = 45 W PEP, I_{DQ} = 350 mA, f1 = 930.0 MHz, f2 = 930.1 MHz and f1 = 960.0 MHz, f2 = 960.1 MHz)	IRL	—	13	—	dB
Power Output, 1 dB Compression Point (V_{DD} = 28 Vdc, P_{out} = 45 W CW, I_{DQ} = 350 mA, f1 = 945.0 MHz)	P_{1dB}	—	55	—	W
Common–Source Amplifier Power Gain (V_{DD} = 28 Vdc, P_{out} = 45 W CW, I_{DQ} = 350 mA, f1 = 945.0 MHz)	G_{ps}	—	18	—	dB
Drain Efficiency (V_{DD} = 28 Vdc, P_{out} = 45 W CW, I_{DQ} = 350 mA, f1 = 945.0 MHz)	η	—	60	—	%
Output Mismatch Stress (V_{DD} = 28 Vdc, P_{out} = 45 W CW, I_{DQ} = 350 mA, f = 945.0 MHz, VSWR = 10:1, All Phase Angles at Frequency of Tests)	Ψ	No Degradation In Output Power			



B1	Short Ferrite Bead Surface Mount	Z4	0.360″ x 0.320″ Microstrip
B2	Long Ferrite Bead Surface Mount	Z5	0.240″ x 0.320″ x 0.620″, Taper
C1, C7, C13, C14	47 pF Chip Capacitors, B Case	Z6	0.140″ x 0.620″ Microstrip
C2, C3, C11	0.8–8.0 pF Gigatrim Variable Trim Capacitors	Z7	0.510″ x 0.620″ Microstrip
C4, C5, C8, C9	10 pF Chip Capacitors, B Case	Z8	0.330″ x 0.320″ Microstrip
C6, C15, C16	10 μF, 35 V Tantalum Surface Mount Chip Capacitors	Z9	0.140″ x 0.320″ Microstrip
C10	2.2 pF Chip Capacitor, B Case	Z10	0.070″ x 0.080″ Microstrip
C12	0.7 pF Chip Capacitor, B Case – MRF9045LS	Z11	0.240″ x 0.080″ Microstrip
	1.3 pF Chip Capacitor, B Case – MRF9045	Z12	0.140″ x 0.080″ Microstrip
C17	220 μF, 50 V Electrolytic Capacitor	Z13	0.930″ x 0.080″ Microstrip
L1, L2	12.5 nH Surface Mount Inductors, Coilcraft	Z14	0.180″ x 0.080″ Microstrip
Z1	0.260″ x 0.080″ Microstrip	Z15	0.350″ x 0.080″ Microstrip
Z2	0.610″ x 0.120″ Microstrip	PCB	Arlon GX–0300–55–22, 0.03″, ε_r = 2.55
Z3	0.260″ x 0.320″ Microstrip		

Figure 1. 930 – 960 MHz Broadband Test Circuit Schematic

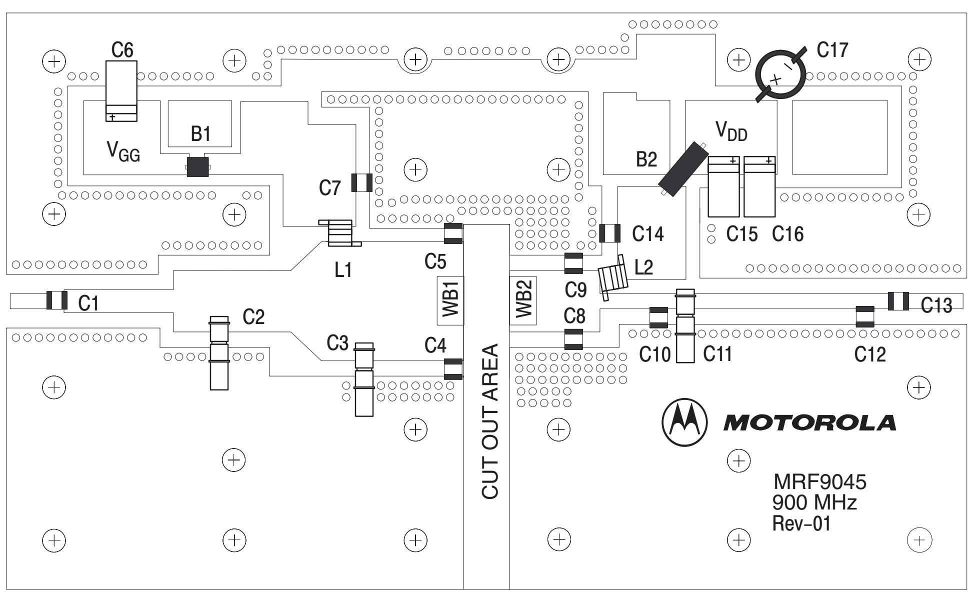


Figure 2. 930 – 960 MHz Broadband Test Circuit Component Layout

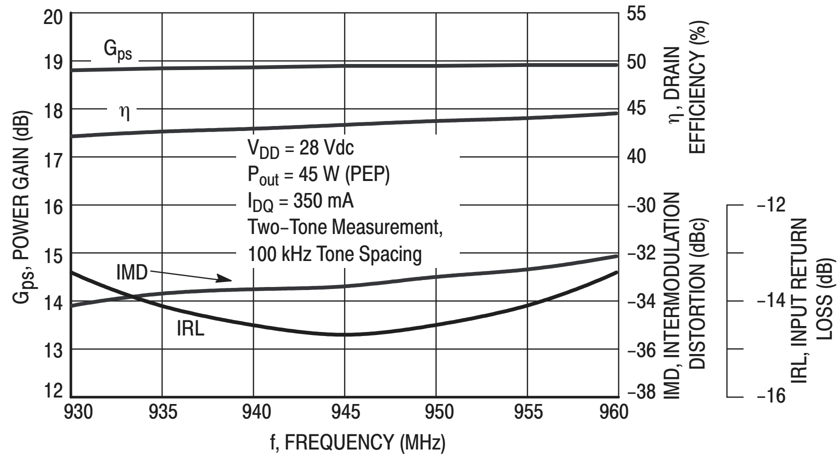


Figure 3. Class AB Broadband Circuit Performance

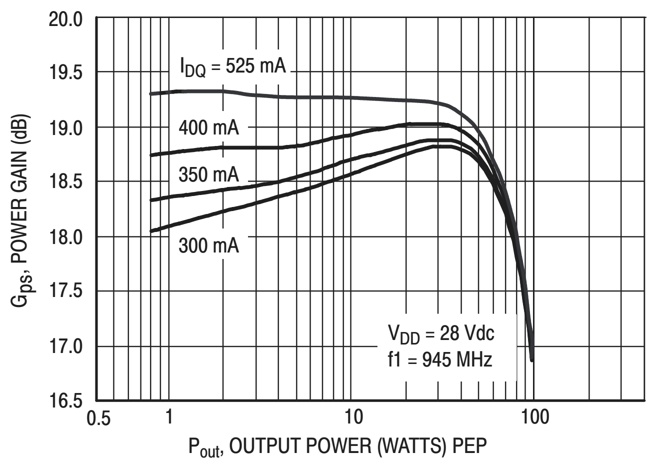


Figure 4. Power Gain versus Output Power

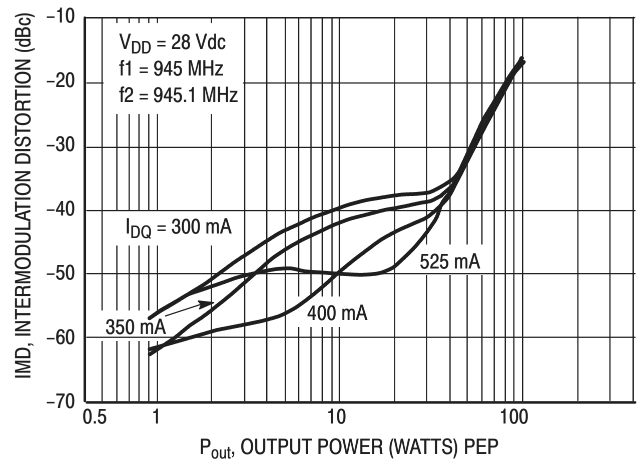


Figure 5. Intermodulation Distortion versus Output Power

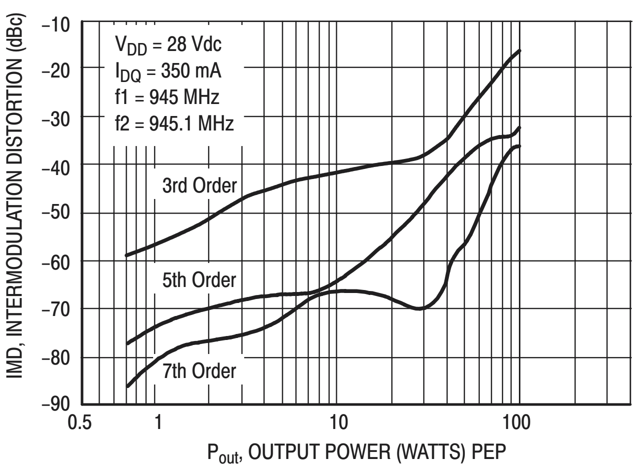


Figure 6. Intermodulation Distortion Products versus Output Power

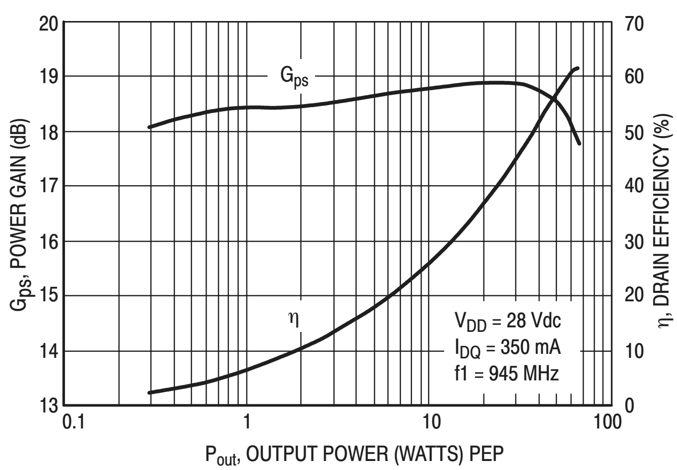
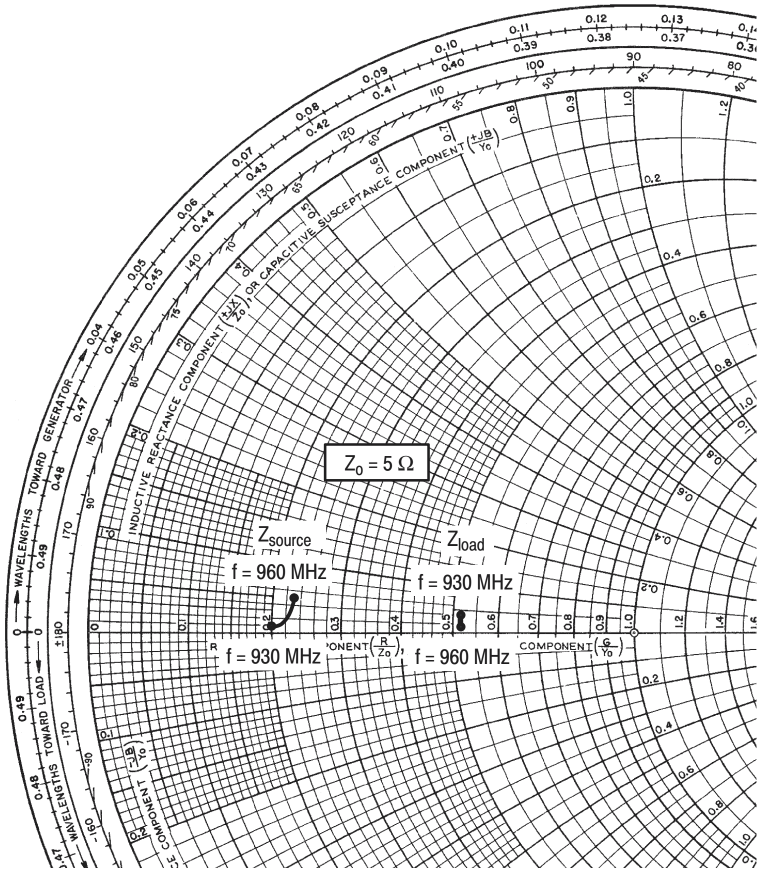


Figure 7. Power Gain, Efficiency versus Output Power



V_{DD} = 28 V, I_{DQ} = 350 mA, P_{out} = 45 W PEP

f MHz	Z_{source} Ω	Z_{load} Ω
930	1.02 + j0.06	2.6 + j0.20
945	1.10 + j0.11	2.6 + j0.16
960	1.15 + j0.25	2.6 + j0.10

Z_{source} = Test circuit impedance as measured from gate to ground.

Z_{load} = Test circuit impedance as measured from drain to ground.

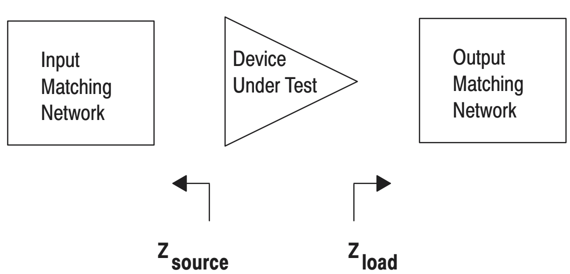
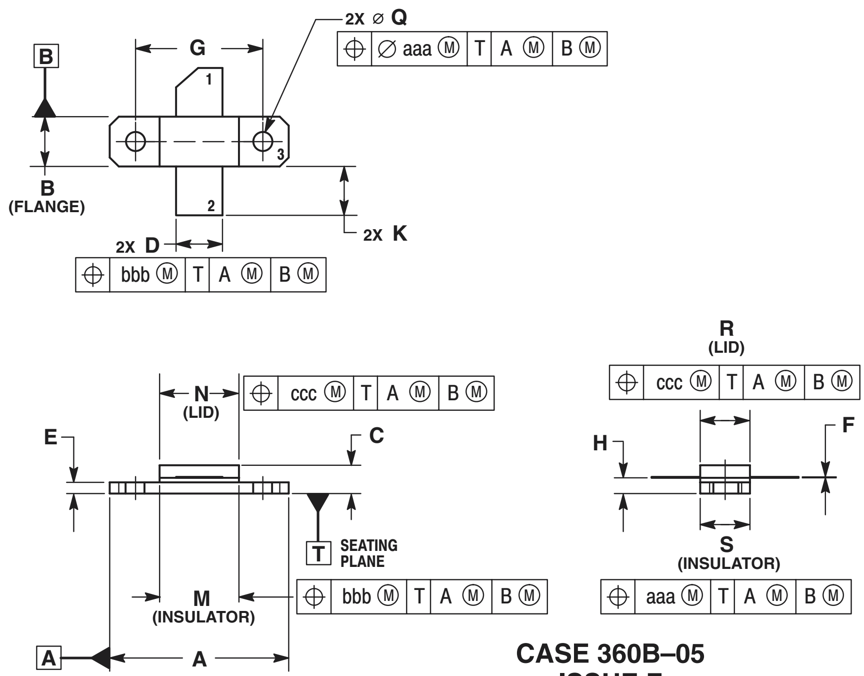


Figure 8. Series Equivalent Input and Output Impedance

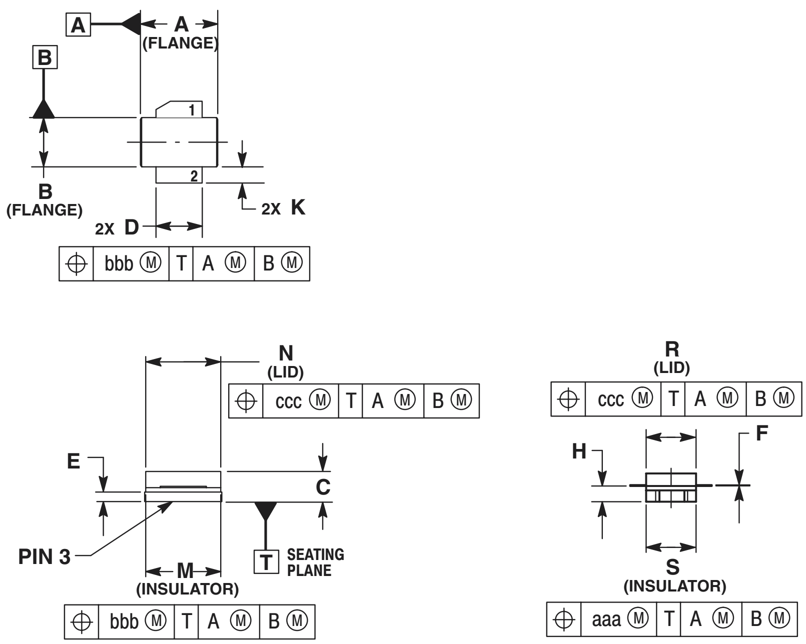


NOTES:
1. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M–1994.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.795	0.805	20.19	20.45
B	0.225	0.235	5.72	5.97
C	0.125	0.175	3.18	4.45
D	0.210	0.220	5.33	5.59
E	0.055	0.065	1.40	1.65
F	0.004	0.006	0.10	0.15
G	0.562 BSC		14.28 BSC	
H	0.077	0.087	1.96	2.21
K	0.220	0.250	5.59	6.35
M	0.355	0.365	9.02	9.27
N	0.357	0.363	9.07	9.22
Q	0.125	0.135	3.18	3.43
R	0.227	0.233	5.77	5.92
S	0.225	0.235	5.72	5.97
aaa	0.005 REF		0.13 REF	
bbb	0.010 REF		0.25 REF	
ccc	0.015 REF		0.38 REF	

STYLE 1:
PIN 1. DRAIN
2. GATE
3. SOURCE

CASE 360B–05
ISSUE F
NI–360
MRF9045R1



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	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.375	0.385	9.53	9.78
B	0.225	0.235	5.72	5.97
C	0.105	0.155	2.67	3.94
D	0.210	0.220	5.33	5.59
E	0.035	0.045	0.89	1.14
F	0.004	0.006	0.10	0.15
H	0.057	0.067	1.45	1.70
K	0.085	0.115	2.16	2.92
M	0.355	0.365	9.02	9.27
N	0.357	0.363	9.07	9.22
R	0.227	0.23	5.77	5.92
S	0.225	0.235	5.72	5.97
aaa	0.005 REF		0.13 REF	
bbb	0.010 REF		0.25 REF	
ccc	0.015 REF		0.38 REF	

STYLE 1:
PIN 1. DRAIN
2. GATE
3. SOURCE

CASE 360C–05
ISSUE D
NI–360S
MRF9045LSR1

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